



DC COMPONENTS CO., LTD.

RECTIFIER SPECIALISTS

1N60P

TECHNICAL SPECIFICATIONS OF SMALL SIGNAL SCHOTTKY DIODES

FEATURES

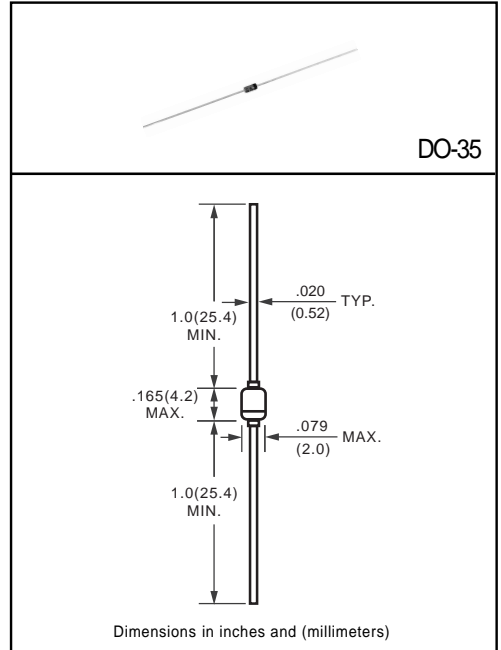
- * Metal silicon junction, majority carrier conduction.
- * High current capability, low forward voltage drop.
- * Extremely low reverse current I_R
- * Ultra speed switching characteristics
- * Small temperature coefficient of forward characteristics
- * Satisfactory Wave detection efficiency
- * For use in RECORDER, TV, RADIO, TELEPHONE as detectors, super high speed switching circuits, small current rectifier

MECHANICAL DATA

- * *Case:* DO-35 glass case
- * *Polarity:* color band denotes cathode end
- * *Weight:* 0.1178 grams approx.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.



ABSOLUTE RATINGS(LIMITING VALUES)

PARAMETERS		SYMBOL	VALUE	UNITS
Repetitive Peak Reverse Voltage		V_{RRM}	30	Volts
Forward Continuous Current	$T_A=25^\circ C$	I_F	50	mA
Peak Forward Surge Current(t=1S)		I_{FSM}	400	mA
Storage and junction Temperature Range		T_{STG}/T_J	-65 to +125	°C
Maximum Lead Temperature for Soldering during 10S at 4mm from Case		T_L	230	°C

ELECTRICAL CHARACTERISTICS

PARAMETERS	TEST CONDITIONS	SYMBOL	VALUE		UNITS
			TYP.	MAX.	
Forward Voltage	$I_F=1mA$	V_F	0.26	0.5	Volts
	$I_F=200mA$		0.70	1.0	
Reverse Current	$V_R=15V$	I_R	5.0	10	µA
Junction Capacitance	$V_R=10V$ $f=1MHz$	C_J	10		pF
Detection Efficiency	$V_I=3V$ $f=30MHz$ $C_L=10pF$ $R_L=3.8K\Omega$	η	60		%
Reverse Recovery time	$I_F=I_R=1mA$ $I_{rr}=1mA$ $R_C=100\Omega$	t_{rr}		1	ns
Junction Ambient Thermal Resistance		$R_{\theta JA}$	400		°C/W

RATING AND CHARACTERISTIC CURVES (1N60P)

FIG. 1 - FORWARD CURRENT VERSUS FORWARD VOLTAGE (TYPICAL VALUES)

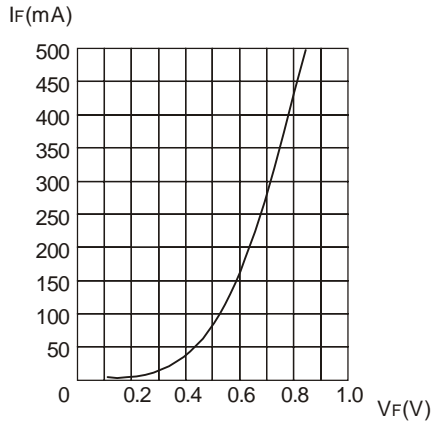


FIG. 2 - REVERSE CURRENT VERSUS CONTINUOUS REVERSE VOLTAGE

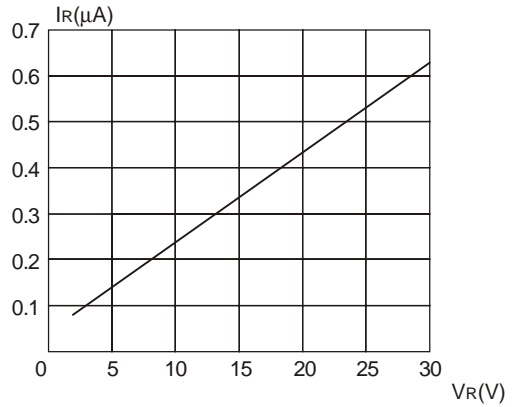


FIG. 3 - JUNCTION CAPACITANCE VERSUS CONTINUOUS REVERSE APPLIED VOLTAGE

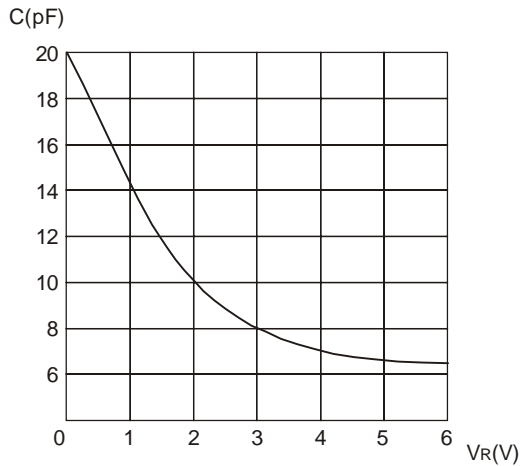


FIG. 4 - DETECTION EFFICIENCY MEASUREMENT CIRCUIT

